

Table 1 Properties of materials in current integrated high-Q microresonators at 1550 nm							
Material	Growth method	Structure	n_o	Reported n_2 ($10^{-20} \text{ m}^2 \text{ W}^{-1}$)	n_2 ($10^{-20} \text{ m}^2 \text{ W}^{-1}$)	Q_{abs} (M)	σ_{abs} (dB m^{-1})
SiO ₂	Wet oxidation	Amorphous	1.44	2.2	-	3915 ± 177	0.0065 ± 0.0003
Si ₃ N ₄	LPCVD	Amorphous	2.00	24	22.2 ± 1.3	287 ± 51	0.122 ± 0.022
Al _{0.2} Ga _{0.8} As	MBE	Crystal	3.28	2600	1658 ± 98	2.04 ± 0.16	28.4 ± 2.2
Ta ₂ O ₅	IBS	Amorphous	2.06	62	27.3 ± 3.1	2.36 ± 0.28	15.4 ± 1.8